

In the Claims

Please replace all prior versions, and listings, of claims in the application with the following list of claims:

1. (Previously Presented) A voltage-controlled monolithic component of triac type, formed in a substrate of a first conductivity type, including:

first and second vertical thyristors, a first main electrode of the first thyristor, on a front surface side of the component, corresponding to a first region of a first conductivity type formed in a first well of a second conductivity type, said first well corresponding to a first main electrode of the second thyristor, the first well containing a second region of the first conductivity type; and

a pilot structure including, on the front surface side, above an extension of a second main electrode region of the second thyristor, a second well of the second conductivity type containing third and fourth regions of the first conductivity type, the third region and a portion of the second well being connected to a gate terminal, the fourth region being connected to the second region.

2. (Previously Presented) The component of claim 1, wherein the component is surrounded at its periphery with a wall of the second conductivity type extending from one surface to the other of the component.

3. (Previously Presented) The component of claim 2, wherein, on the front surface side, the first well includes an extension which surrounds the second well.

4. (Previously Presented) The component of claim 3, wherein an external periphery of the first well and of its extension is surrounded with a lightly-doped ring of the second conductivity type.

5. (New) A voltage-controlled monolithic component of triac type, formed in a substrate of a first conductivity type comprising:

a first well of a second conductivity type comprising a first and second region of the first conductivity type;

a pilot structure comprising a second well of the second conductivity type and a third and fourth region of the first conductivity type, wherein the third region and a portion of the second well are connected to a gate terminal, and wherein the second region and fourth region are connected; and

a first thyristor comprising a first main electrode corresponding to the first region and a second thyristor comprising a first main electrode corresponding to the first well, wherein an extension of a second main electrode of the second thyristor is located below the pilot structure.

6. (New) The component of claim 5, wherein the component is surrounded at its periphery with a wall of the second conductivity type extending from one surface to the other of the component.

7. (New) The component of claim 6, wherein, on the front surface side, the first well includes an extension which surrounds the second well.

8. (New) The component of claim 7, wherein an external periphery of the first well and of its extension is surrounded with a lightly-doped ring of the second conductivity type.